

Silicon Switching Diode

1N4148
or
1N4148-1

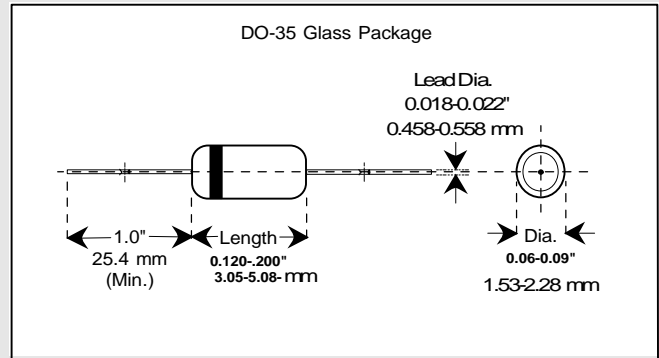
DO-35 Glass Package

Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- LL-34/35 MELF SMD available
- Hermetic Glass Body
- Available up to JANTXV-1 levels
- "S" level screening available to Source Control Drawings-



Maximum Ratings	Symbol	Value	Unit	
Peak Inverse Voltage	PIV	100 (Min).	Volts	
Average Rectified Current	I _{avg}	200	mAmps	
Continuous Forward Current	I _{Fdc}	300	mAmps	
Peak Surge Current (t _{peak} = 1 sec.)	I _{peak}	1.0	Amp	
BKC Power Dissipation T _L =50 °C, L = 3/8" from body	P _{tot}	500	mWatts	
Operating Temperature Range	T _{Op}	-65 to +200	°C	
Storage Temperature Range	T _{St}	-65 to +200	°C	
Electrical Characteristics @ 25 °C*	Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ I _F = 10 mA	V _F	***	1.00	Volts
Breakdown Voltage @ I _R = 5 μA	PIV	75		Volts
Breakdown Voltage @ I _R = 100 μA	PIV	100		Volts
Reverse Leakage Current @ V _R = 75 V	I _R		5 (100 @ 150 °C)	μA
Capacitance @ V _R = 0 V, f = 1mHz	C _T		4.0	pF
Reverse Recovery time (note 1)	t _{rr}		4.0	nSecs

Note 1: Per Method 4031-A with I_F = 10 mA, V_R = 6 V, R_L = 100 Ohms. * UNLESS OTHERWISE SPECIFIED